

**40V N-CHANNEL ENHANCEMENT MODE MOSFET**

**Product Summary**

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$ $T_A = 25^\circ C$
40V	27mΩ @ $V_{GS} = 10V$	8.0A
	47mΩ @ $V_{GS} = 4.5V$	6.1A

**Features and Benefits**

- Low on-resistance
- Fast switching speed
- “Green” component and RoHS compliant (Note 1)
- **Qualified to AEC-Q101 Standards for High Reliability**

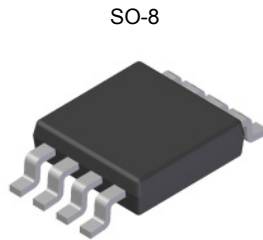
**Description and Applications**

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

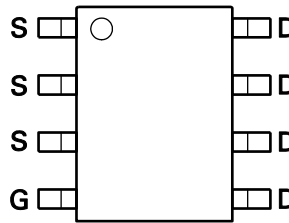
- Motor control
- Backlighting
- DC-DC Converters
- Power management functions

**Mechanical Data**

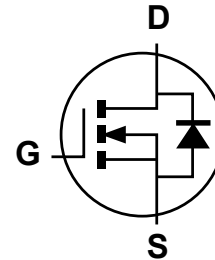
- Case: SO-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See diagram below
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)



Top View



Top View



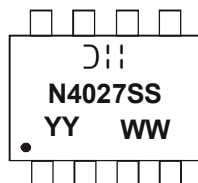
Equivalent Circuit

**Ordering Information** (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN4027SSS-13	N4027SS	13	12	2,500

Note: 1. Diodes, Inc. defines “Green” products as those which are RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.’s “Green” Policy can be found on our website. For packaging details, go to our website.

**Marking Information**



⌋⌋ = Manufacturer’s Marking  
 N4027SS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 09 = 2009)  
 WW = Week (01-53)

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

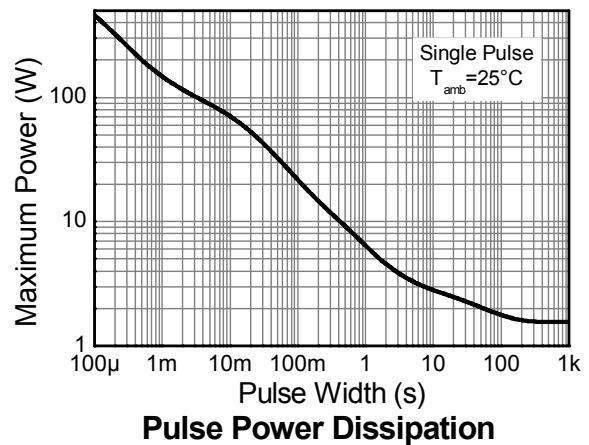
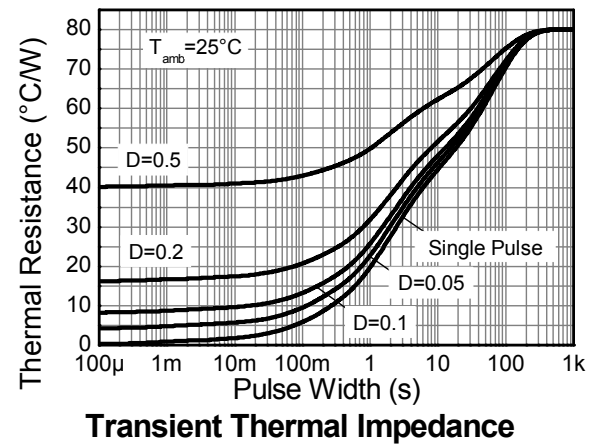
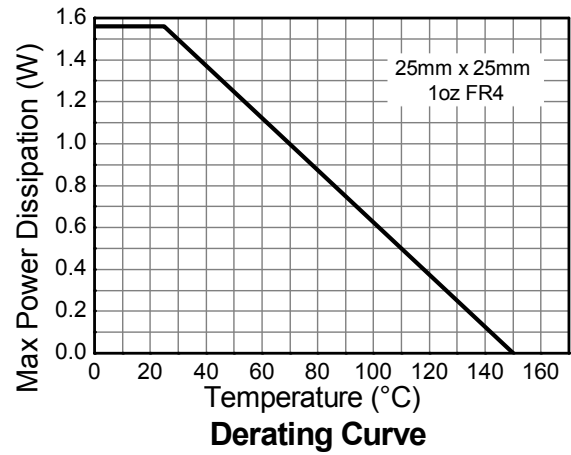
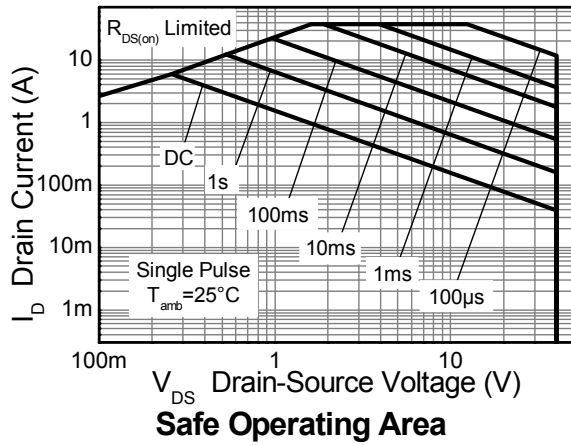
Characteristic			Symbol	Value	Unit
Drain-Source voltage			V <sub>DSS</sub>	40	V
Gate-Source voltage			V <sub>GS</sub>	±20	V
Continuous Drain current	V <sub>GS</sub> = 10V	(Note 2)	I <sub>D</sub>	8.0	A
		T <sub>A</sub> = 70°C (Note 4)		6.5	
		(Note 3)		6.0	
Pulsed Drain current	V <sub>GS</sub> = 10V	(Note 5)	I <sub>DM</sub>	37	A
Continuous Source current (Body diode)			I <sub>S</sub>	4.2	A
Pulsed Source current (Body diode)			I <sub>SM</sub>	37	A

**Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation	(Note 3)	P <sub>D</sub>	1.56	W
			12.5	
Linear derating factor	(Note 4)		2.8	mW/°C
			22.5	
Thermal Resistance, Junction to Ambient	(Note 3)	R <sub>θJA</sub>	80	°C/W
	(Note 4)		44.5	
Thermal Resistance, Junction to Lead	(Note 6)	R <sub>θJL</sub>	35	
Operating and storage temperature range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

- Notes:
- AEC-Q101 V<sub>GS</sub> maximum is ±16V.
  - For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  - Same as note (3), except the device is measured at t ≤ 10 sec.
  - Same as note (3), except the device is pulsed with D= 0.02 and pulse width 300 μs. The pulse current is limited by the maximum junction temperature.
  - Thermal resistance from junction to solder-point (at the end of the drain lead).

**Thermal Characteristics**

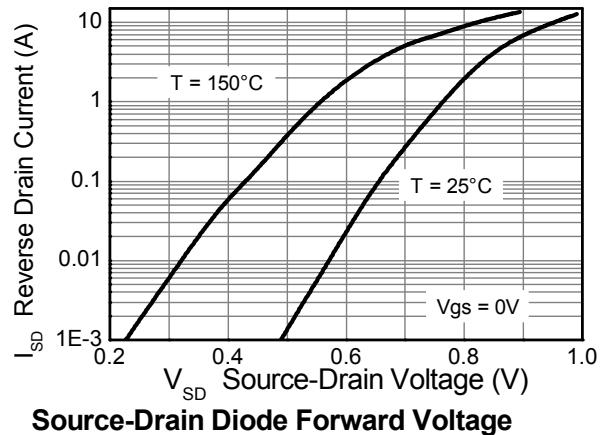
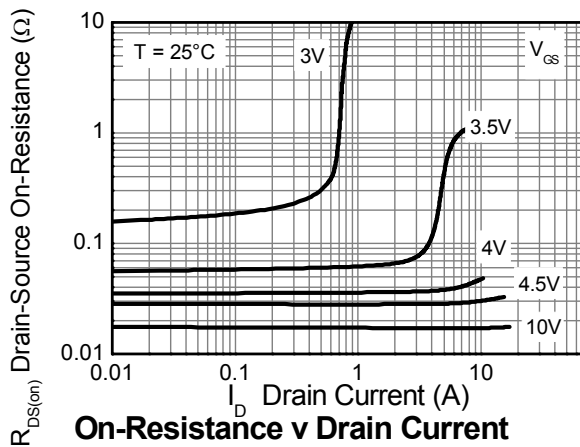
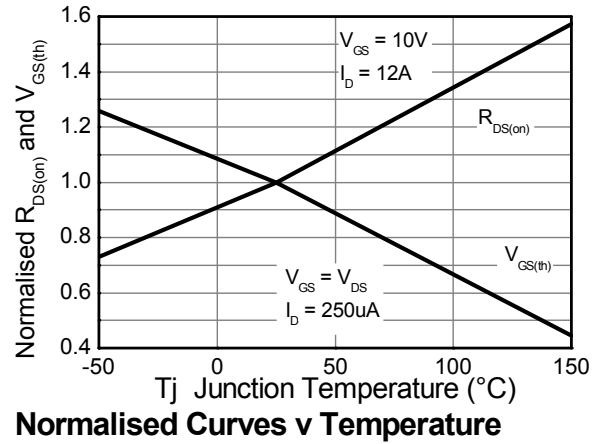
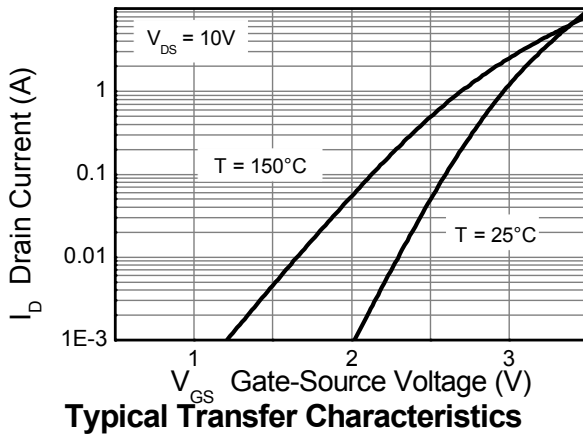
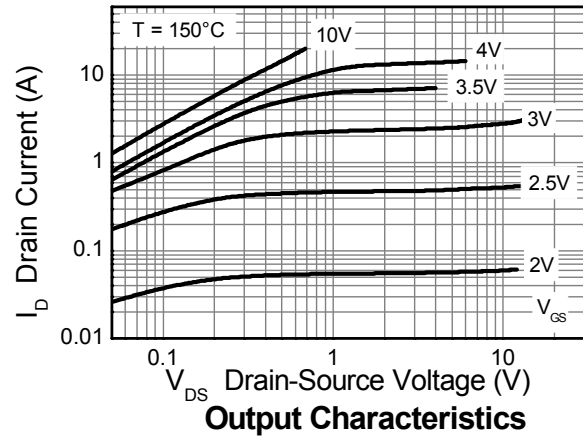
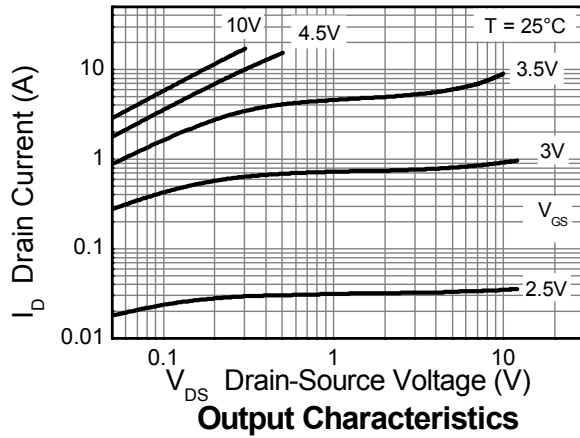


**Electrical Characteristics** @ $T_A = 25^\circ\text{C}$  unless otherwise specified

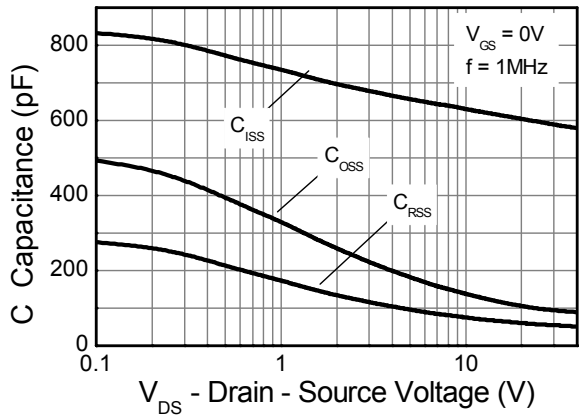
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	40	—	—	V	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	0.5	$\mu\text{A}$	$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	3.0	V	$I_D = 250\mu\text{A}, V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 7)	$R_{DS(on)}$	—	0.017	0.027	$\Omega$	$V_{GS} = 10\text{V}, I_D = 7\text{A}$
			0.031	0.047		$V_{GS} = 4.5\text{V}, I_D = 6\text{A}$
Forward Transconductance (Notes 7 & 8)	$g_{fs}$	—	22.8	—	S	$V_{DS} = 15\text{V}, I_D = 7\text{A}$
Diode Forward Voltage (Note 7)	$V_{SD}$	—	0.85	1.1	V	$I_S = 7\text{A}, V_{GS} = 0\text{V}$
Reverse recovery time (Note 8)	$t_{rr}$	—	12.2	—	ns	$I_S = 2.5, di/dt = 100\text{A}/\mu\text{s}$
Reverse recovery charge (Note 8)	$Q_{rr}$	—	5.4	—	nC	
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	—	604	—	pF	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	$C_{oss}$	—	106	—	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	59.6	—	pF	
Total Gate Charge (Note 9)	$Q_g$	—	6.3	—	nC	$V_{GS} = 4.5\text{V}$
Total Gate Charge (Note 9)	$Q_g$	—	12.9	—	nC	$V_{GS} = 10\text{V}$
Gate-Source Charge (Note 9)	$Q_{gs}$	—	2.4	—	nC	
Gate-Drain Charge (Note 9)	$Q_{gd}$	—	3	—	nC	
Turn-On Delay Time (Note 9)	$t_{D(on)}$	—	3.1	—	ns	$V_{DD} = 20\text{V}, V_{GS} = 10\text{V}$ $I_D = 1\text{A}, R_G = 6.0\Omega$
Turn-On Rise Time (Note 9)	$t_r$	—	3.1	—	ns	
Turn-Off Delay Time (Note 9)	$t_{D(off)}$	—	15.4	—	ns	
Turn-Off Fall Time (Note 9)	$t_f$	—	7.5	—	ns	

- Notes:
7. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$
  8. For design aid only, not subject to production testing.
  9. Switching characteristics are independent of operating junction temperatures.

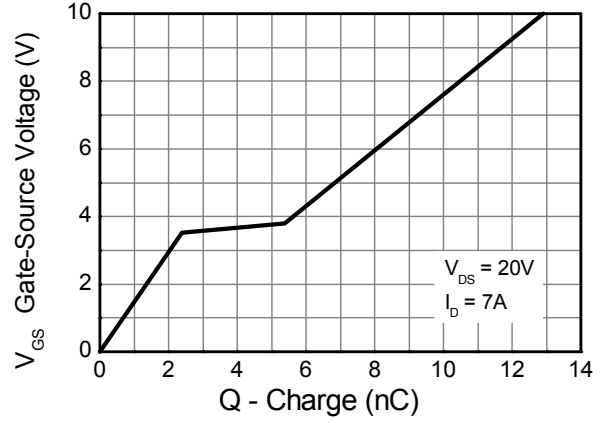
**Typical Characteristics**



**Typical Characteristics - continued**

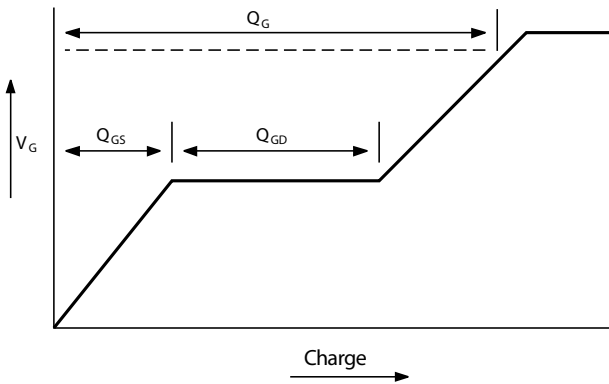


**Capacitance v Drain-Source Voltage**

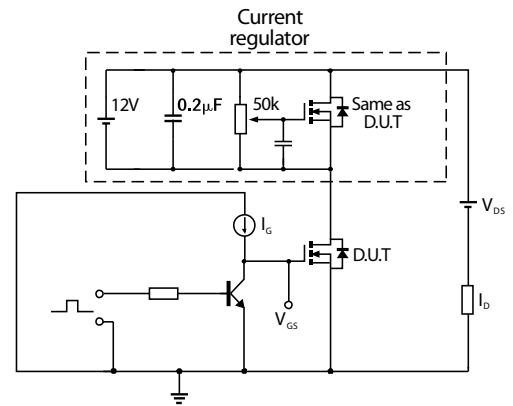


**Gate-Source Voltage v Gate Charge**

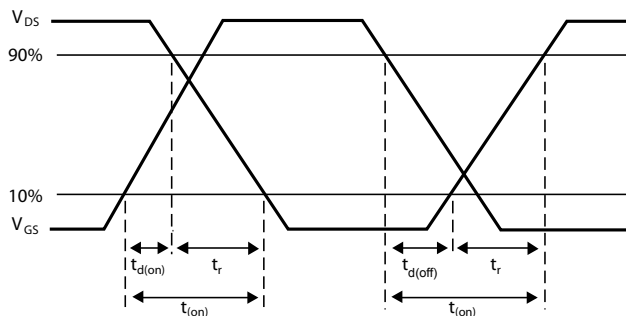
**Test Circuits**



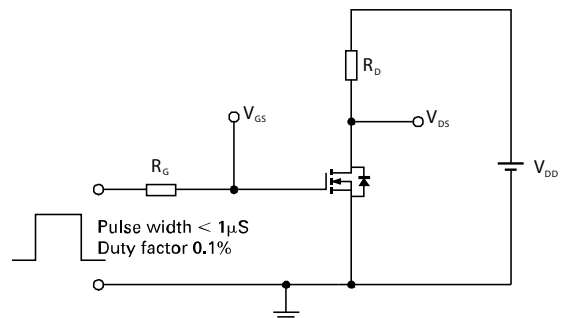
**Basic gate charge waveform**



**Gate charge test circuit**

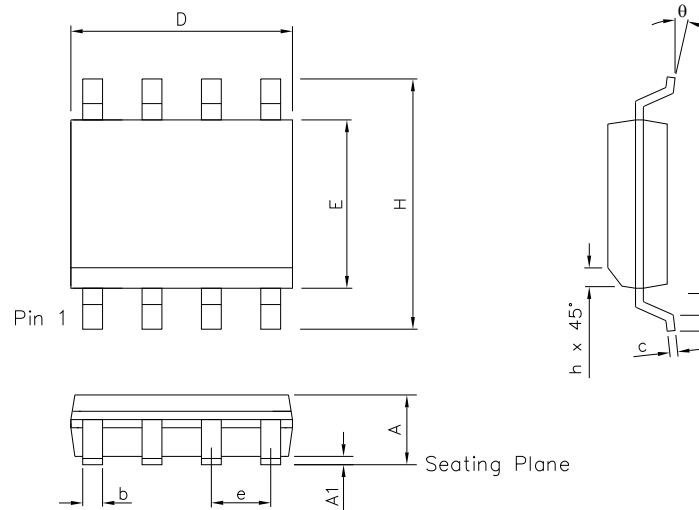


**Switching time waveforms**



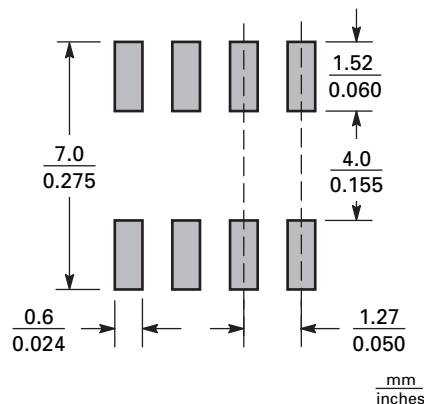
**Switching time test circuit**

**Package Outline Dimensions**



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.053	0.069	1.35	1.75	e	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	c	0.008	0.010	0.19	0.25
H	0.228	0.244	5.80	6.20	theta	0°	8°	0°	8°
E	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

**Suggested Pad Layout**



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